

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
150V	90mΩ @ V _{GS} = 10V	27A
	100mΩ @ V _{GS} = 6V	26A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low R_{DS(ON)} – Minimizes Power Losses
- Low Q_g – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.**

Description and Applications

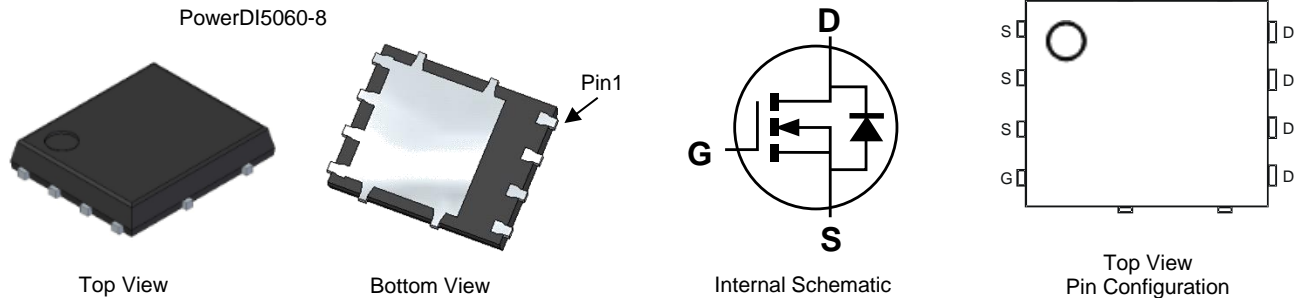
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Engine Management Systems
- Body Control Electronics
- DC/DC Converters

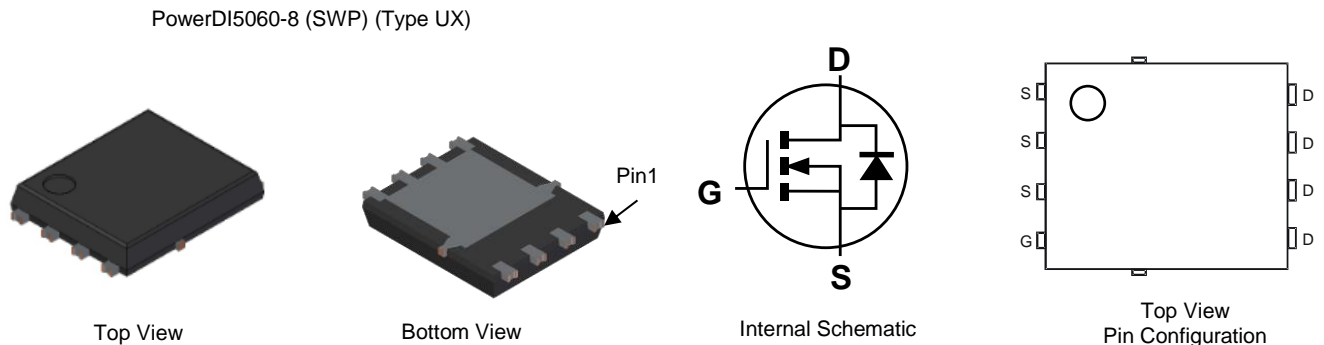
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208③
- Weight: 0.097 grams (Approximate)

Site1:



Site2:



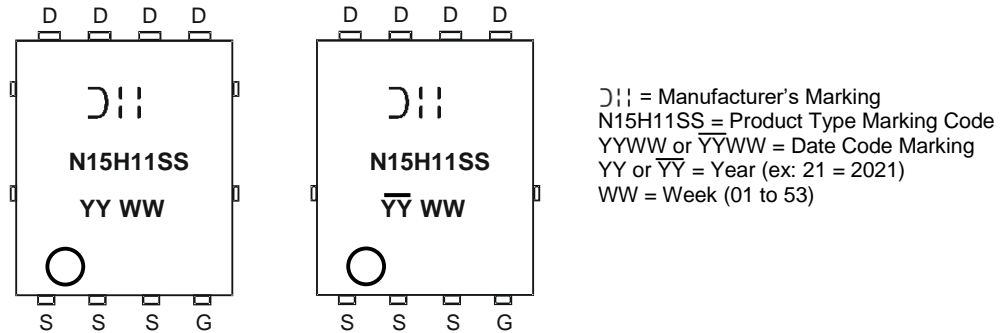
Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

PowerDI is a registered trademark of Diodes Incorporated.

Ordering Information (Note 4)

Part Number	Case	Packaging
DMNH15H110SPS-13	PowerDI5060-8 PowerDI5060-8 (SWP) (Type UX)	2500/Tape & Reel

Note: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	150	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 7) $V_{GS} = 10\text{V}$	Steady State	$T_C = +25^\circ\text{C}$	I_D	27	A
		$T_C = +100^\circ\text{C}$		19	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	108	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	27	A
Pulsed Source Current (10 μs Pulse, Duty Cycle = 1%)			I_{SM}	108	A
Avalanche Current (Note 8) $L = 3\text{mH}$			I_{AS}	9	A
Avalanche Energy (Note 8) $L = 3\text{mH}$			E_{AS}	121.5	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	98	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	44	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 7)	$R_{\theta JC}$	1.5	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	150	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 120V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	2	—	4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	70	90	mΩ	V _{GS} = 10V, I _D = 2A
		—	76	100		V _{GS} = 6V, I _D = 2A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 2A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	989	—	pF	V _{DS} = 75V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{oss}	—	63	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	38.3	—	pF	
Gate Resistance	R _g	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	25.5	—	nC	V _{DS} = 75V, I _D = 4A
Total Gate Charge (V _{GS} = 6V)	Q _g	—	17.8	—	nC	
Gate-Source Charge	Q _{gs}	—	4.0	—	nC	
Gate-Drain Charge	Q _{gd}	—	10	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	18	—	ns	V _{DD} = 75V, V _{GS} = 10V R _G = 24Ω, I _D = 4A
Turn-On Rise Time	t _R	—	46	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	76	—	ns	
Turn-Off Fall Time	t _F	—	59	—	ns	I _F = 4A, di/dt=100A/μs
Reverse Recovery Time	t _{RR}	—	42	—	ns	
Reverse Recovery Charge	Q _{RR}	—	66	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

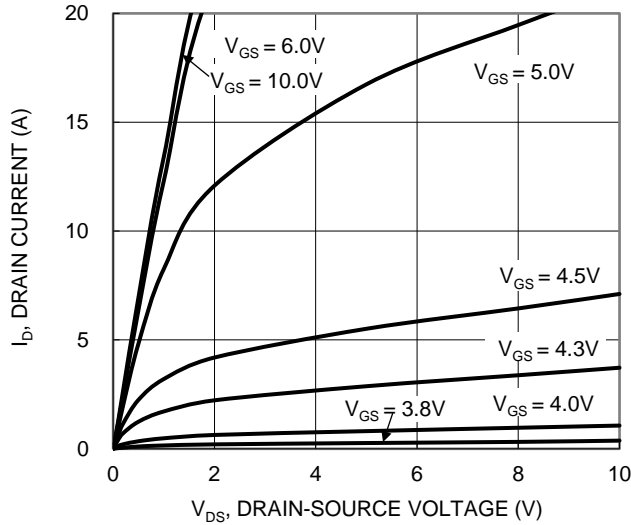


Figure 1. Typical Output Characteristic

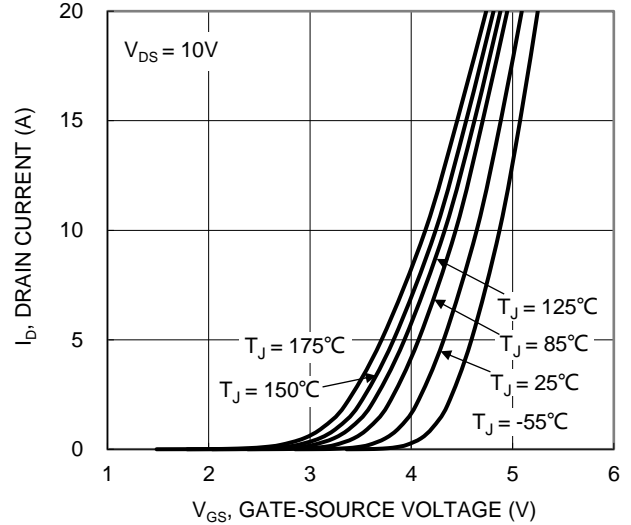


Figure 2. Typical Transfer Characteristic

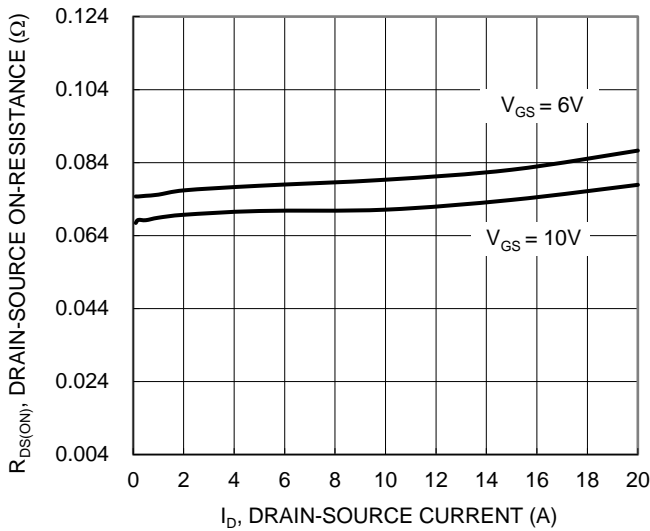


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

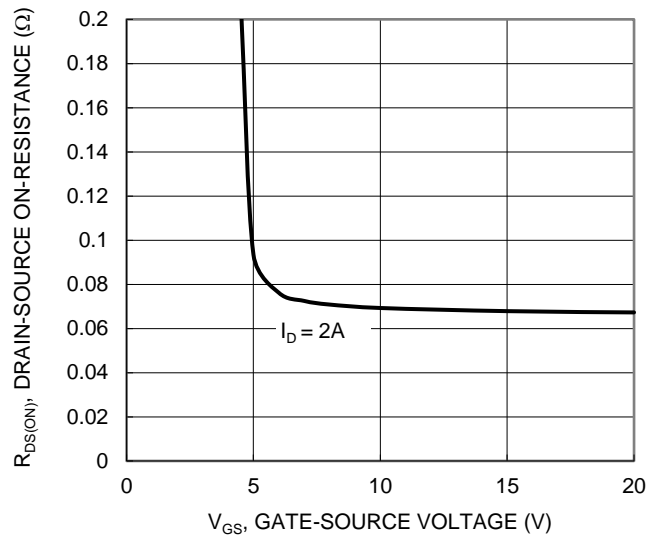


Figure 4. Typical Transfer Characteristic

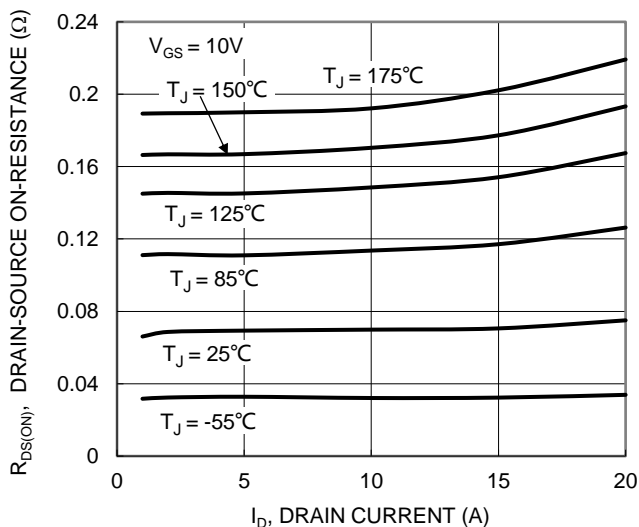


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

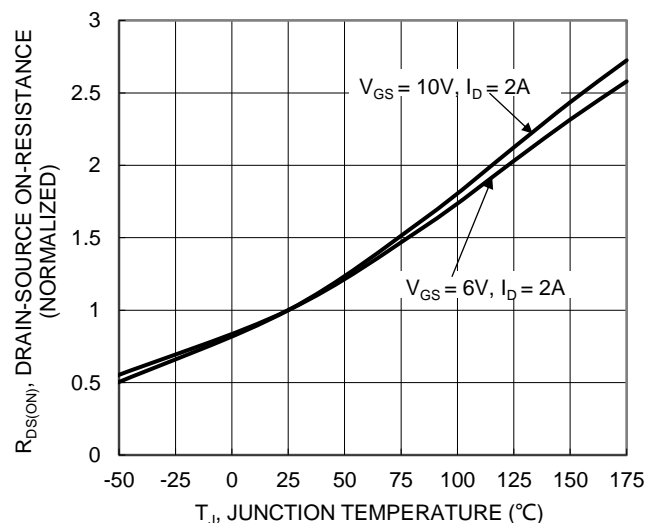


Figure 6. On-Resistance Variation with Temperature

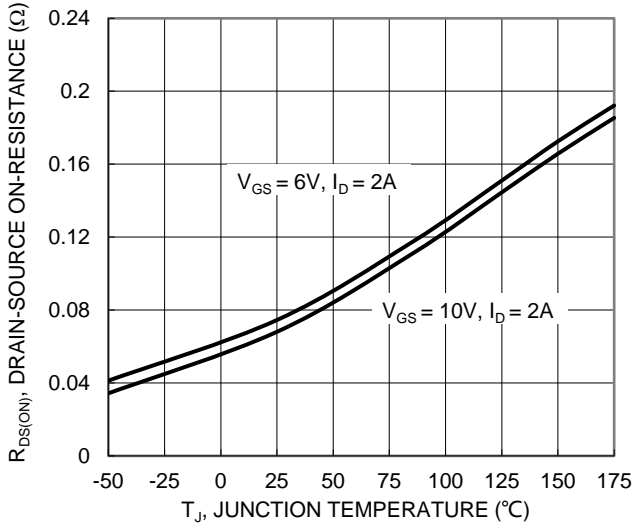


Figure 7. On-Resistance Variation with Temperature

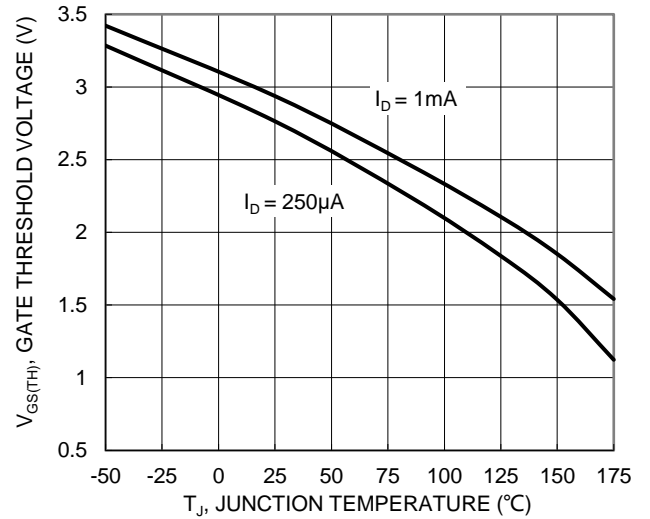


Figure 8. Gate Threshold Variation vs. Junction Temperature

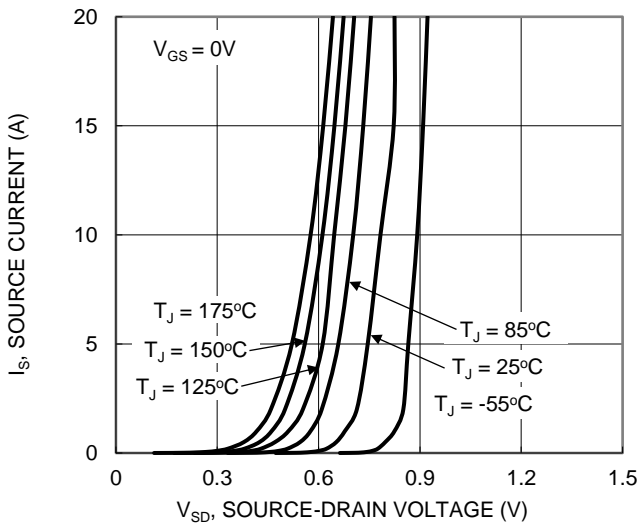


Figure 9. Diode Forward Voltage vs. Current

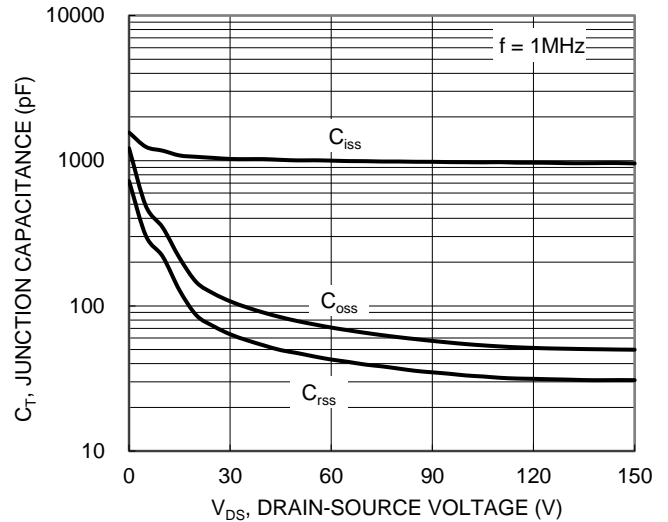


Figure 10. Typical Junction Capacitance

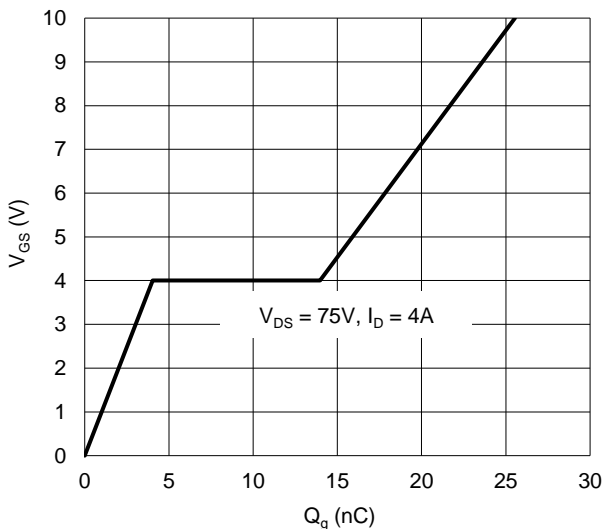


Figure 11. Gate Charge

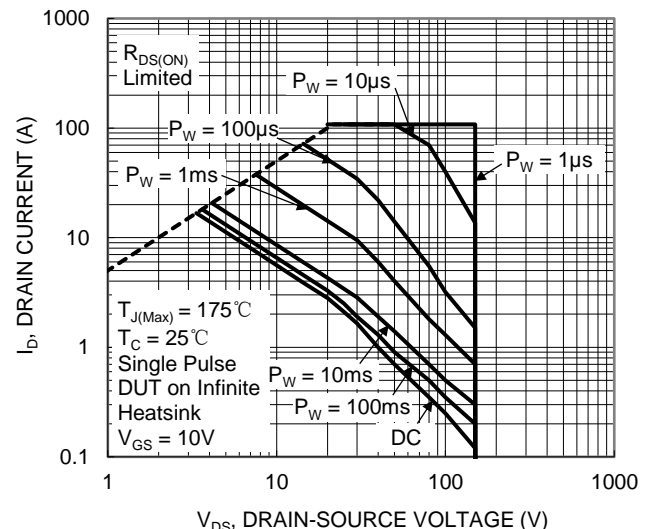


Figure 12. SOA, Safe Operation Area

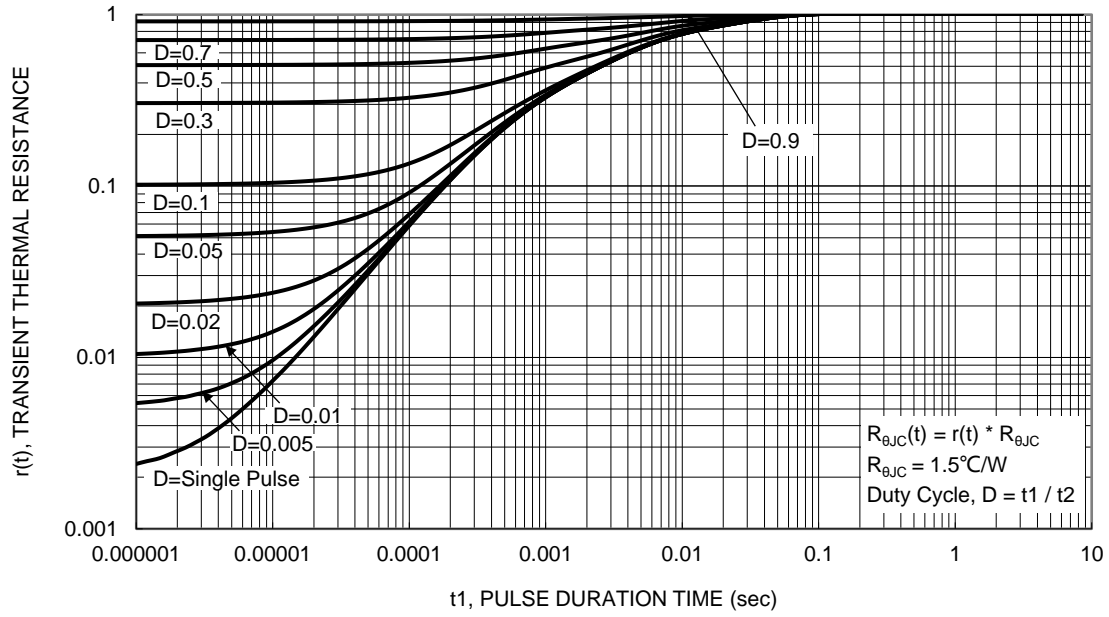


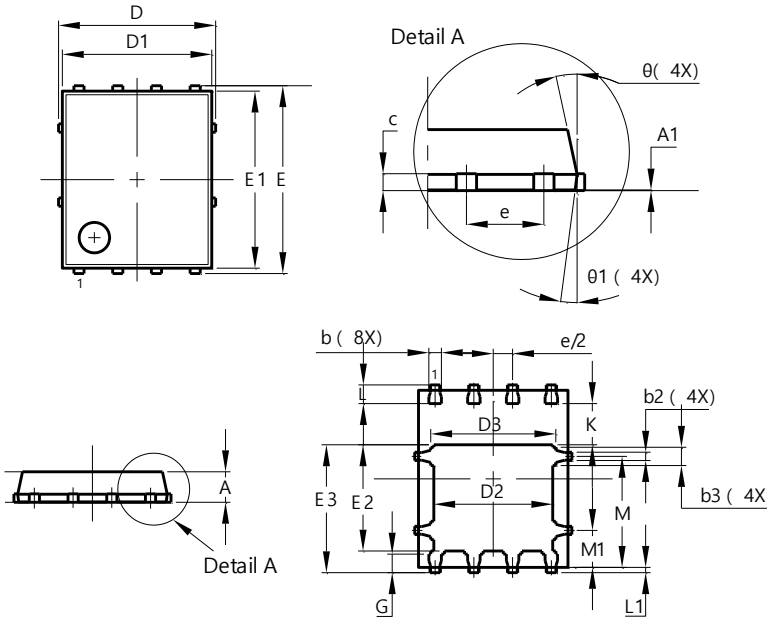
Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site1:

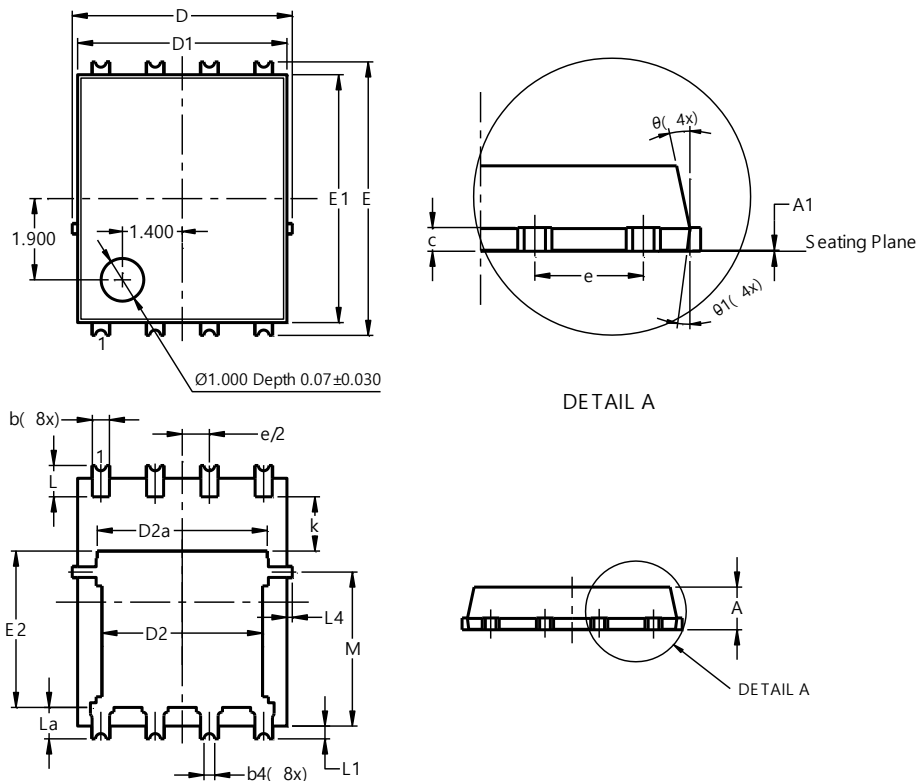
PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51		
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

Site2:

PowerDI5060-8 (SWP) (Type UX)



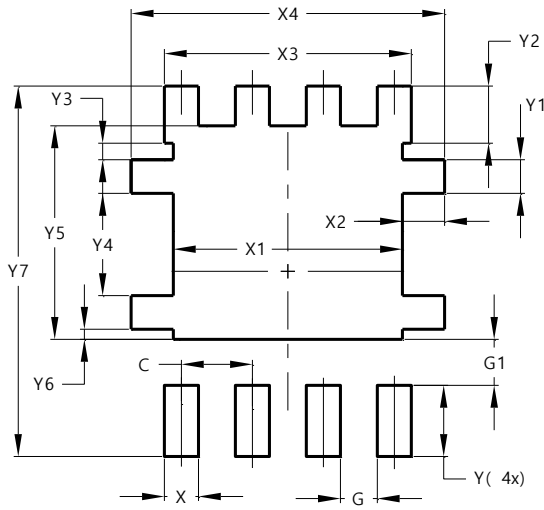
PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
theta	10°	12°	11°
theta1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site1:

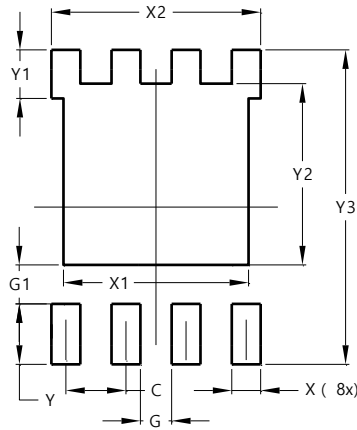
PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site2:

PowerDI5060-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610

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